

20 V, 800 mA dual N-channel Trench MOSFET Rev. 1 — 13 September 2011

Product data sheet

1. **Product profile**

1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in an ultra small and flat lead SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

- ESD protection up to 2 kV
- AEC-Q101 qualified
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	r						
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; \text{ T}_{amb} = 25 \text{ °C}$	<u>[1]</u>	-	-	800	mA
Static charac	teristics (per transistor)						
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I _D = 500 mA; T _j = 25 °C		-	290	380	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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2. Pinning information

Table 2.	Pinning	g information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		54 50
2	G1	gate TR1		
3	D2	drain TR2		
4	S2	source TR2	0	$G1 \xrightarrow{f} G2$
5	G2	gate TR2		
6	D1	drain TR1	SOT666	S1 S2 017aaa256

3. Ordering information

Table 3. Ordering in	nformation		
Type number	Package		
	Name	Description	Version
PMDT290UNE	-	plastic surface-mounted package; 6 leads	SOT666

4. Marking

Table 4.	Marking codes	
Type numb	ber	Marking code
PMDT290U	INE	AE

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	tor					
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C	<u>[1]</u>	-	800	mA
		V_{GS} = 4.5 V; T_{amb} = 100 °C	<u>[1]</u>	-	500	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	3.2	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	330	mW
			[1]	-	390	mW
		T _{sp} = 25 °C		-	1090	mW
Per device						
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	500	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
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Table 5. Limiting values ...continued

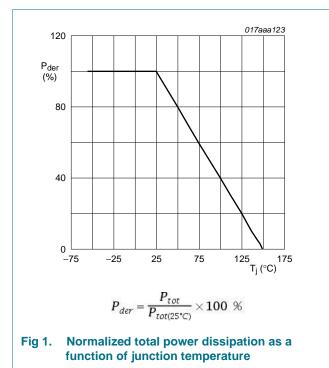
In accordance with the Absolute Maximum Rating System (IEC 60134).

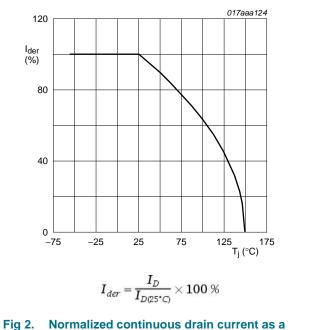
Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode					
I _S	source current	T _{amb} = 25 °C		-	370	mA
ESD maxim	um rating					
V _{ESD}	electrostatic discharge voltage	HBM	[3]	-	2000	V

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

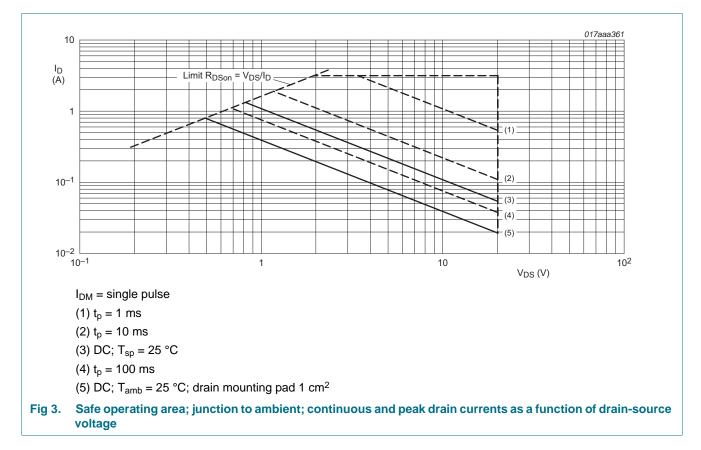




function of junction temperature

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6. Thermal characteristics

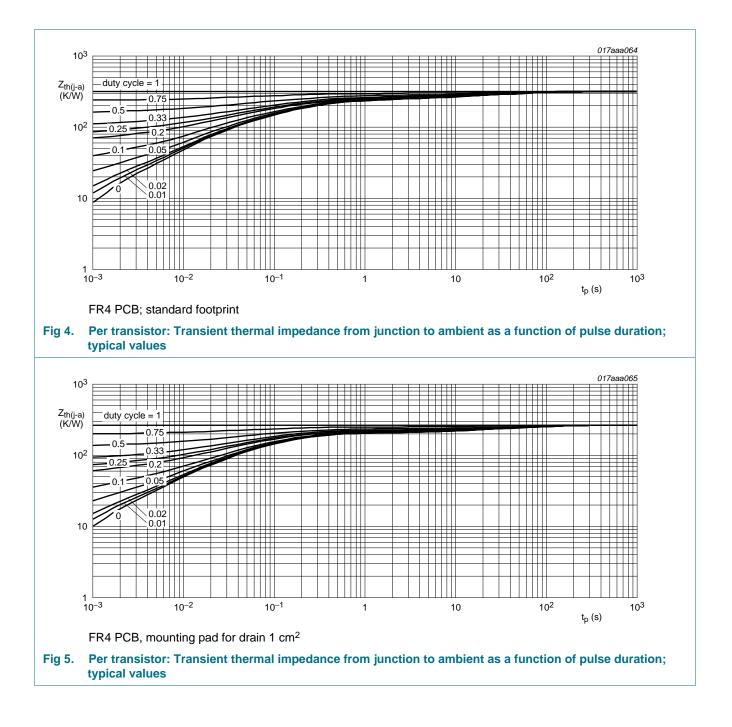
Thermal characteristics						
Parameter	Conditions		Min	Тур	Max	Unit
istor						
thermal resistance	in free air	<u>[1]</u>	-	330	380	K/W
from junction to ambient		[2]	-	280	320	K/W
thermal resistance from junction to solder point			-	-	115	K/W
e						
thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	-	250	K/W
	Parameter istor thermal resistance from junction to ambient thermal resistance from junction to solder point e thermal resistance from junction to solder point	Parameter Conditions istor thermal resistance from junction to ambient in free air thermal resistance from junction to solder point thermal resistance from junction to solder point	Parameter Conditions istor thermal resistance from junction to ambient in free air [1] thermal resistance from junction to solder point in free air [2] thermal resistance from junction to solder point in free air [1] te [1] [1] [1] in free air [1] [1] thermal resistance from junction to solder point in free air [1]	ParameterConditionsMinistorthermal resistance from junction to ambientin free air[1]-[2][2]-thermal resistance from junction to solder pointethermal resistance from junction to solderin free air[1]-thermal resistance from junction to solder pointin free air[1]-	ParameterConditionsMinTypistorthermal resistance from junction to ambientin free air[1]-330[2]-280thermal resistance from junction to solder pointthermal resistance from junction to solder pointthermal resistance from junction to solder pointthermal resistance from junction to solder point	ParameterConditionsMinTypMaxistorthermal resistance from junction to ambientin free air[1]-330380[2]-280320thermal resistance from junction to solder point115ethermal resistance from junction to solder pointin free air[1]250

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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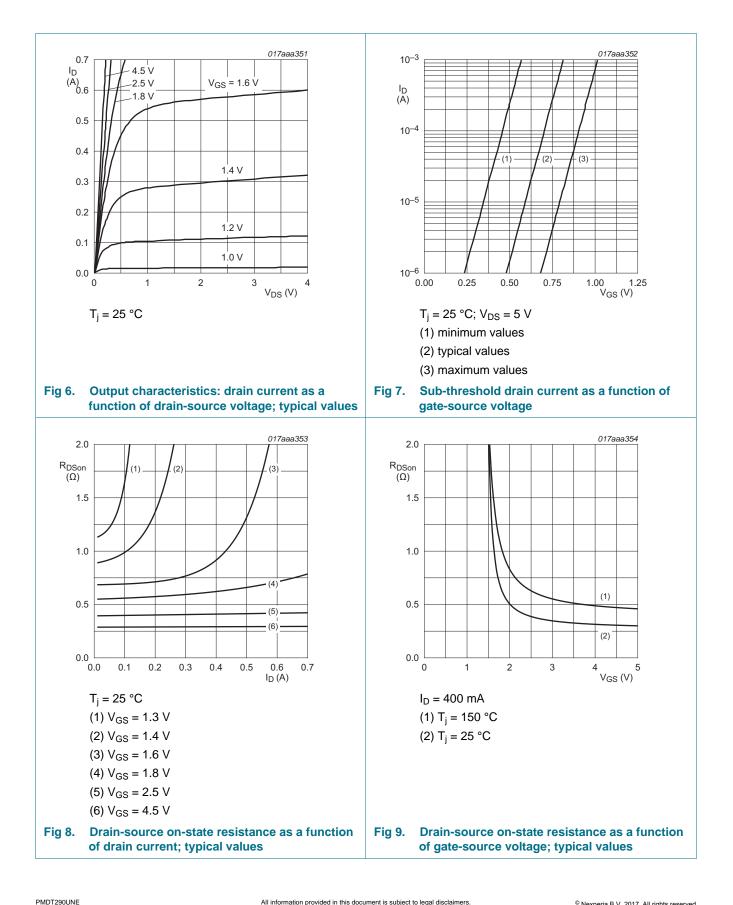
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7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics (per transistor)					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	20	-	-	V
V _{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	0.5	0.75	0.95	V
I _{DSS} drain leakag	drain leakage current	V _{DS} = 20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{DS} = 20 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μA
I _{GSS}	gate leakage current	$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	2	μA
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	-	2	μΑ
		V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	500	nA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	500	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I _D = 500 mA; T _j = 25 °C	-	290	380	mΩ
		V_{GS} = 4.5 V; I _D = 500 mA; T _j = 150 °C	-	460	610	mΩ
		V_{GS} = 2.5 V; I _D = 400 mA; T _j = 25 °C	-	420	620	mΩ
		V_{GS} = 1.8 V; I _D = 100 mA; T _j = 25 °C	-	600	1100	mΩ
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_D = 200 mA; T_j = 25 °C	-	1.6	-	S
Dynamic	characteristics (per transist	or)				
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I_{D} = 500 mA; V_{GS} = 4.5 V;	-	0.45	0.68	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.15	-	nC
Q _{GD}	gate-drain charge		-	0.15	-	nC
C _{iss}	input capacitance	V_{DS} = 10 V; f = 1 MHz; V_{GS} = 0 V;	-	55	83	pF
C _{oss}	output capacitance	T _j = 25 °C	-	15	-	pF
C _{rss}	reverse transfer capacitance		-	7	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; R_L = 250 $\Omega;$ V_{GS} = 4.5 V;	-	6	12	ns
t _r	rise time	R _{G(ext)} = 6 Ω; T _j = 25 °C	-	4	-	ns
t _{d(off)}	turn-off delay time		-	86	172	ns
t _f	fall time		-	31	-	ns
Source-d	rain diode (per transistor)					
V _{SD}	source-drain voltage	I _S = 300 mA; V _{GS} = 0 V; T _i = 25 °C	0.48	0.77	1.2	V

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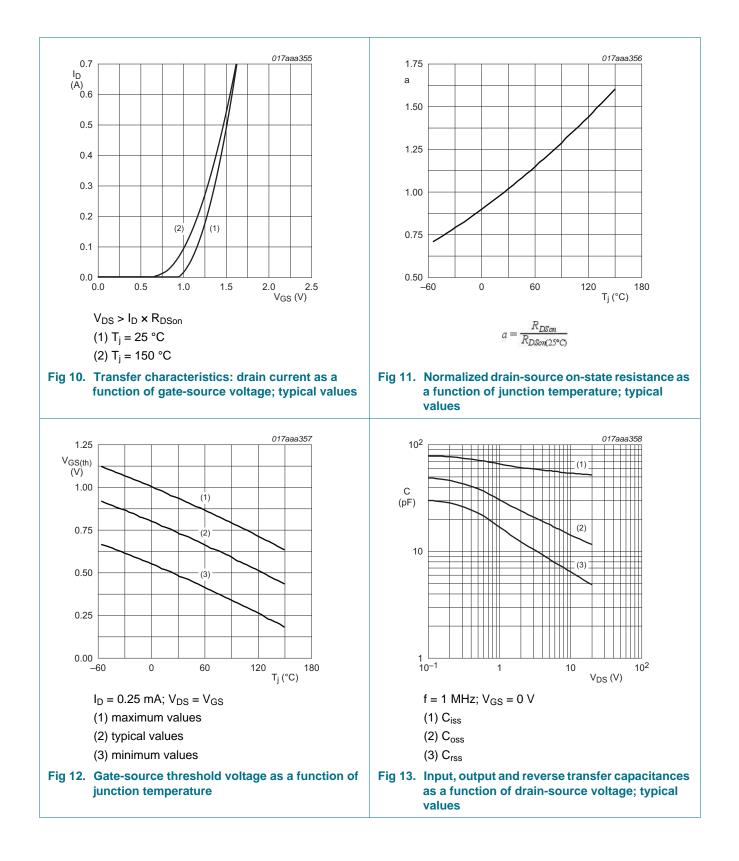
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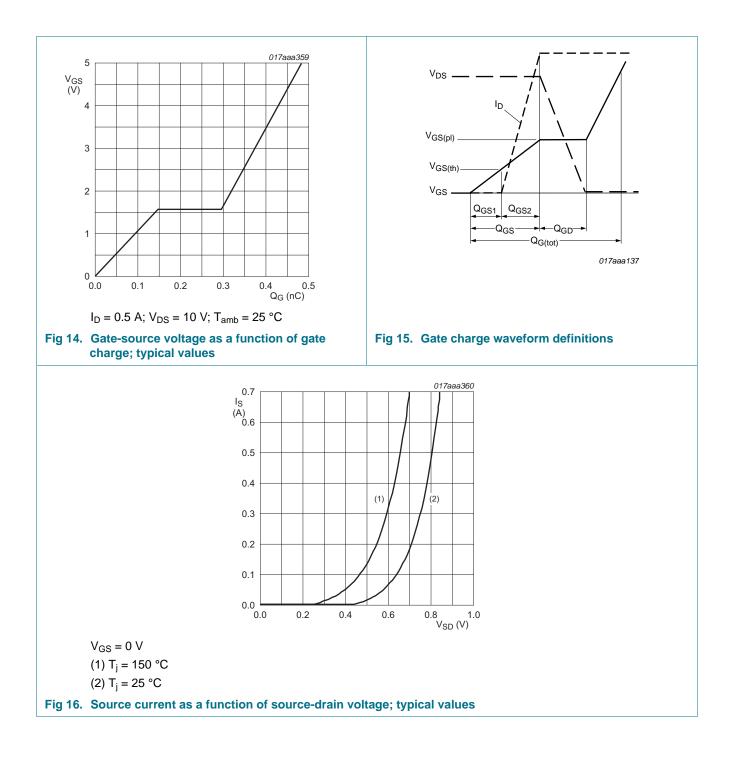
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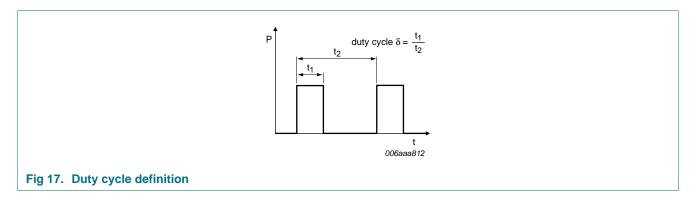
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8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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9. Package outline

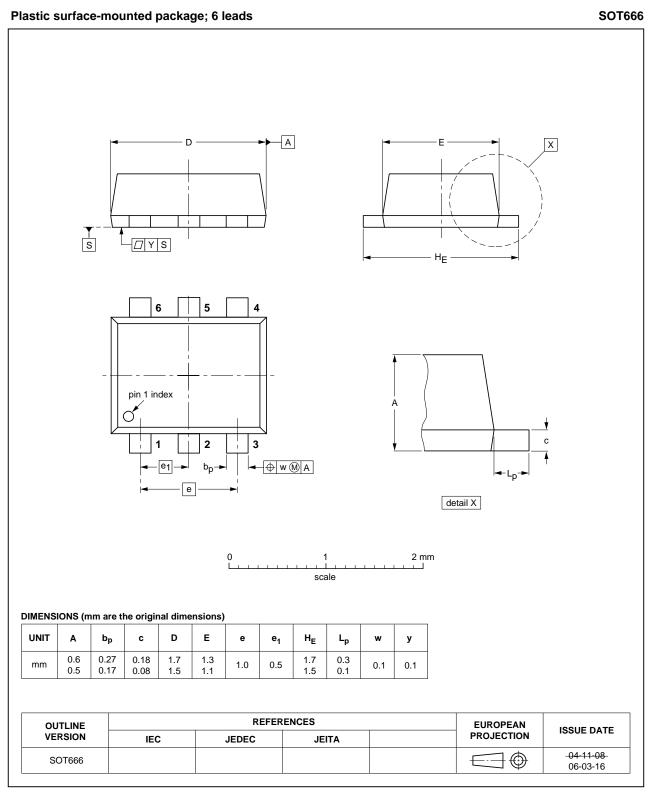


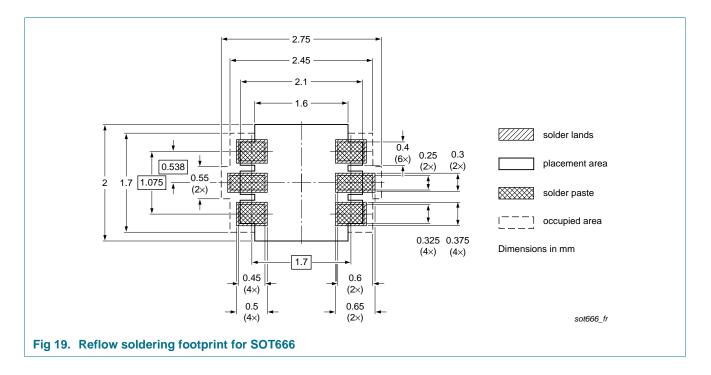
Fig 18. Package outline SOT666

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10. Soldering



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11. Revision history

Table 8. R	. Revision history				
Document I	כ	Release date	Data sheet status	Change notice	Supersedes
PMDT290UN	IE v.1	20110913	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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